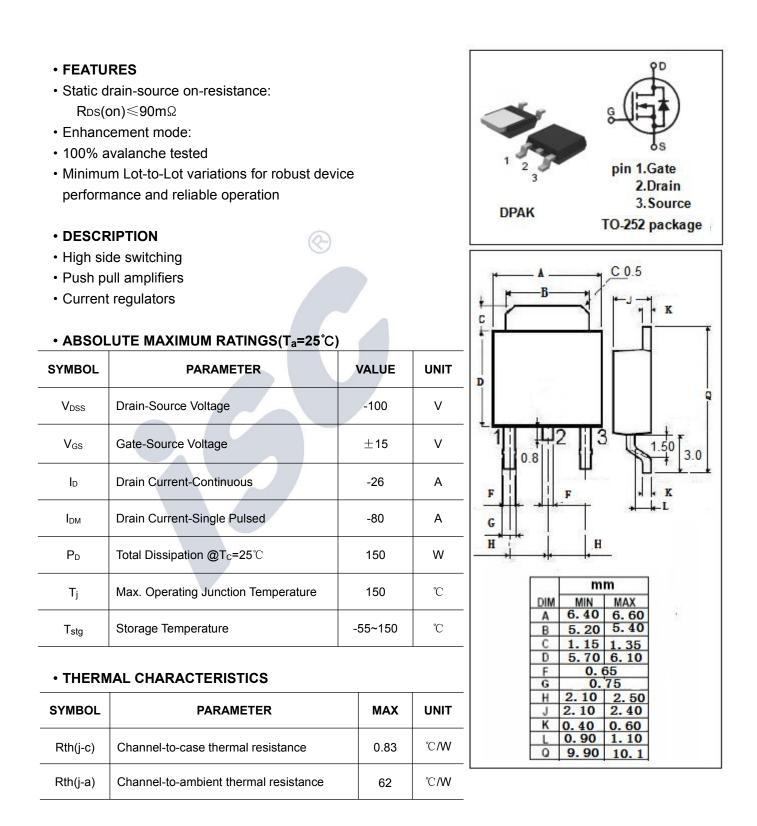


### **INCHANGE SEMICONDUCTOR**

## isc P-Channel MOSFET Transistor

## IXTY26P10T



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# isc P-Channel MOSFET Transistor

# IXTY26P10T

### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = -250 μ A	-100			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	VDS=VGS; I <sub>D</sub> = -250 µ A	-2.0		-4.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = -10V; I <sub>D</sub> = -13A			90	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = ±15V; $V_{DS}$ = 0V			±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =V <sub>DSS</sub> ; V <sub>GS</sub> = 0V			-10	μA
V <sub>SD</sub>	Diode forward voltage	IF=IS; V <sub>GS</sub> = 0V			-1.5	V

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